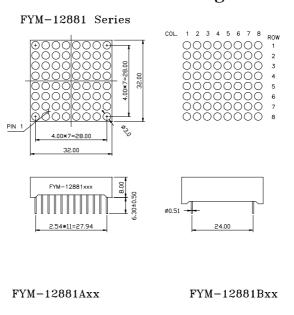


PartNO.:FYM-12881A/BXX-XX

DESCRIPTION

- 32.00mm (1.2") Φ3.0 dot matrix LED display.
- Standard brightness.
- Low current operation.
- Excellent character apperance.
- Easy mounting on P.C.boards or sockets

Package Dimensions &Internal Circuit Diagram



Notes:

- · All dimensions are in millimeters (inches)
- Tolerance is $\pm 0.25(0.01")$ unless otherwise noted.
- · Specificaions are subject to change whitout notice.

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: Absolute maximum ratings ($Ta=25^{\circ}C$)

Dawamatan	Symbol	Test Condition	Va	11- 14	
Parameter			Min	Max	Unit
Reverse Voltage	VR	IR=30μA	5		V
Forward Current IF				30	mA
Power Dissipation Pd					mW
Pulse Current	Ipeak	Duty=0.1mS, 1KHz		150	mA
Operating Temperature	Topr		-40	+85	° C
Storage Temperature	Tstr		-40	+85	° C

• -XX: Surface / Lens color:

Number	0	1	2	3	4	5
Ref Surface Color	White	Black	Gray	Red	Green	
Epoxy Color	Water clear	White diffused	Red Diffused	Green Diffused	Yellow Diffused	



PartNO.:FYM-12881A/BXX-XX

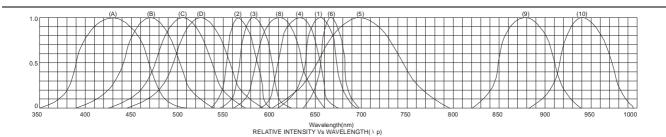
■ Description:

Color Code & Chip characteristics: (Test Condition: IF=20mA)

		Dice	s. (Test Condit			vard	
Emitting Color		Material	Peak Wave Length(^λ P)	Spectral Line halfwidth(Forward Voltage(VF) Unit:V		Luminous Intensity (Iv)
				∆λ1/2 ₎	Тур	Max	Unit:mcd
Н	Red	GaP	700nm	90nm	2.20	2.50	5.0
S, SR	Hi Red	AlGaAs,SH	660nm	20nm	1.80	2.20	15-20
D	Super Red	AlGaAs,DH	660nm	20nm	1.80	2.20	20-30
LR	Ultra Red	AlGaAs,DDH	660nm	20nm	1.90	2.40	26-38
HR	HE Red	GaAsP	640nm	45nm	1.90	2.40	50-80
Е	Orange	GaAsP	630nm	35nm	2.10	2.50	10-20
Α	Amber	GaAsP	610nm	35nm	2.10	2.50	15-20
Υ	Yellow	GaAsP	590nm	35nm	2.10	2.50	15-20
G	Green	GaP	570nm	30nm	2.20	2.50	14-18
Ultra	a brightness						
UH R	Ultra Hi Red	AlGalnP	645nm	20nm	2.10	2.50	80-150
UE	Ultra Orange	AlGalnP	630nm	20nm	2.10	2.50	180-210
UA	Ultra Amber	AlGalnP	610nm	20nm	2.10	2.50	90-120
UY	Ultra Yellow	AlGalnP	590nm	20nm	2.10	2.50	150-200
UG	Ultra Green	AlGalnP	570nm	30nm	2.20	2.50	60-100
PG	Ultra Pure Green	InGaN	520nm	36nm	2.80	3.80	260-310
BG	Ultra Blue Green	InGaN	505nm	36nm	2.80	3.80	260-310
В	Blue	InGaN	430nm	30nm	2.80	3.80	10-20
UB	Ultra Blue	InGaN	470nm	30nm	2.80	3.80	80-90
UB		IIIGain	460nm	30nm	2.80	3.80	80-90
V	UV	InGaN	405nm		2.80	3.80	5-8
W	White	InGaN	X=0.29,y=0.30		2.80	3.80	180-200
U W	Ultra White	InGaN	X=0.29,y=0.30		2.80	3.80	180-200
Segment-to-Segment Luminous Intensity ratio(Iv-M) 1.5:1							

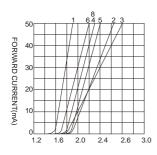
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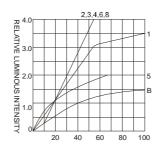


- (1) GaAsP/GaAs 655nm/Red
- (2) GaP 570nm/Yellow Green
- (3) GaAsP/GaP 585nm/Yellow
- (4) GaAsp/GaP 635nm/Orange & Hi-Eff Red
- (5) GaP 700nm/Bright Red
- (6) GaAlAs/GaAs 660nm/Super Red
- (8) GaAsP/GaP 610nm/Super Red

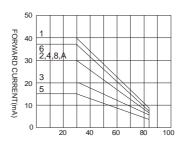
- (9) GaAlAs 880nm
- (10) GaAs/GaAs & GaAlAs/GaAs 940nm
- (A) GaN/SiC 430nm/Blue
- (B) InGaN/SiC 470nm/Blue
- (C) InGaN/SiC 505nm/Ultra Green
- (D) InGaAl/SiC 525nm/Ultra Green



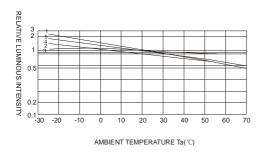
FORWARD VOLTAGE (Vf) FORWARD CURRENT VS. FORWARD VOLTAGE

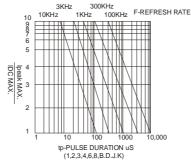


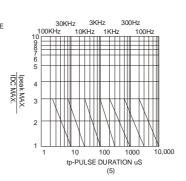
FORWARD CURRENT (mA) RELATIVE LUMINOUS INTENSITY VS. FORWARD CURRENT



AMBIENT TEMPERATURE Ta(°C) FORWARD CURRENT VS. AMBIENT TEMPERATURE





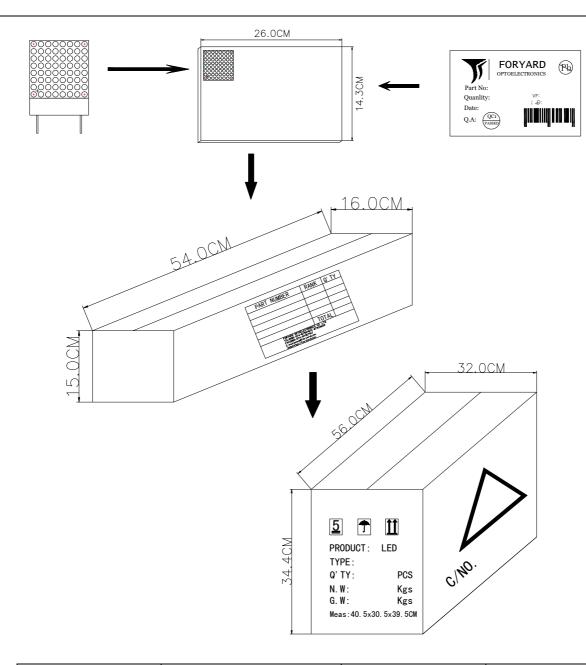


NOTE:25 ℃ free air temperature unless otherwise specified

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PartNO.:FYM-12881A/BXX-XX



type	QTY/foam(pcs)	QTY /Bundle (pcs)	QTY / CARTONDimension
FYM-12881ABxx-xx	4*8=32	32*16=512	512*4=2048

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